

## SEMIPACK<sup>®</sup> 1

# Modules with Thyristor and Free-Wheeling Diode

### **SKNH 56**

#### **Features**

- Heat transfer through ceramic isolated metal baseplate
- Hard soldered joints for high reliability
- UL recognized, file no. E 63 532
- Electrical data see also data sheet SKKH 57

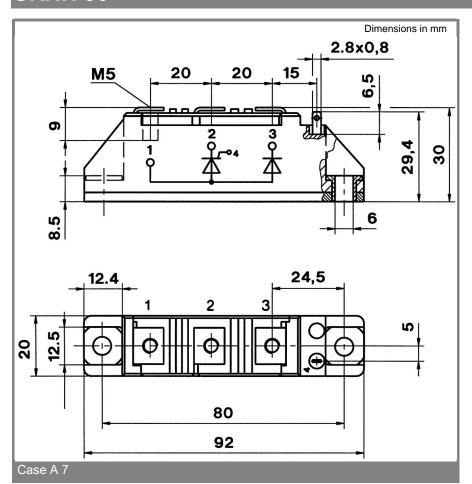
### **Typical Applications**

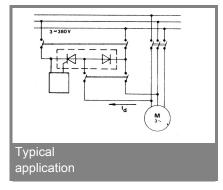
 Special modules for DC braking of AC induction motors

$V_{RSM}$	$V_{RRM}, V_{DRM}$	I <sub>TRMS</sub> = 95 A (maximum value for continuous operation)		
V	V	I <sub>TAV</sub> = 50 A (sin. 180; T <sub>c</sub> = 85 °C)		
1300	1200	SKNH 56/12E		
1500	1400	SKNH 56/14E		
1700	1600	SKNH 56/16E		
1900	1800	SKNH 56/18E		

Symbol	Conditions	Values	Units
I <sub>TAV</sub>	sin. 180; T <sub>c</sub> = 85 (100) °C	50 (35 )	Α
I <sub>D</sub>	P3/120; T <sub>a</sub> = 45 °C;	70	Α
I <sub>TSM</sub>	T <sub>vi</sub> = 25 °C; 10 ms	1500	Α
TOW	T <sub>vi</sub> = 125 °C; 10 ms	1250	Α
i²t	T <sub>vi</sub> = 25 °C; 8,3 10 ms	11000	A²s
	T <sub>vi</sub> = 125 °C; 8,3 10 ms	8000	A²s
V <sub>T</sub>	T <sub>vi</sub> = 25 °C; I <sub>T</sub> = 200 A	max. 1,65	V
V <sub>T(TO)</sub>	T <sub>vi</sub> = 125 °C	max. 0,9	V
r <sub>T</sub>	T <sub>vi</sub> = 125 °C	max. 3,5	mΩ
$I_{DD}$ ; $I_{RD}$	$T_{vj} = 25 \text{ °C}; V_{RD} = V_{RRM}; V_{DD} = V_{DRM}$	max. 15	mA
t <sub>gd</sub>	$T_{vj}$ = 25 °C; $I_G$ = 1 A; $di_G/dt$ = 1 A/ $\mu$ s	1	μs
$t_{gr}$	$V_{D} = 0.67 * V_{DRM}$	2	μs
(di/dt) <sub>cr</sub>	T <sub>vi</sub> = 125 °C	max. 100	A/µs
(dv/dt) <sub>cr</sub>	T <sub>vi</sub> = 125 °C	max. 1000	V/µs
tq	T <sub>vi</sub> = 125 °C	50 150	μs
I <sub>H</sub>	T <sub>vi</sub> = 25 °C; typ. / max.	/ 250	mA
IL	$T_{vj} = 25 {}^{\circ}\text{C};  R_{G} = 33 \Omega;  \text{typ.}  /  \text{max.}$	/ 600	mA
V <sub>GT</sub>	T <sub>vi</sub> = 25 °C; d.c.	min. 3	V
$I_{GT}$	$T_{vj} = 25  ^{\circ}\text{C}; \text{d.c.}$	min. 150	mA
$V_{GD}$	$T_{vj} = 125 ^{\circ}\text{C}; \text{d.c.}$	max. 0,25	V
$I_{GD}$	T <sub>vj</sub> = 125 °C; d.c.	max. 6	mA
R <sub>th(j-c)</sub>	cont.; per thyristor / per diode	0,57	K/W
R <sub>th(j-c)</sub>	sin. 180; per thyristor / per diode	0,6	K/W
R <sub>th(j-c)</sub>	sin. 180; per module	0,3	K/W
R <sub>th(c-s)</sub>	per thyristor / per module	0,2 / 0,1	K/W
T <sub>vi</sub>		- 40 <b>+</b> 125	°C
T <sub>stg</sub>		- 40 + 125	°C
V <sub>isol</sub>	a. c. 50 Hz; r.m.s.; 1 s / 1 min.	3600 / 3000	V~
M <sub>s</sub>	to heatsink	5 ± 15 %	Nm
M <sub>t</sub>	to terminals	5 ± 15 %	Nm
a		5 * 9,81	m/s²
m	approx.	120	g
Case		A 7	
		1	







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